

ABSTRACT AMENDMENTS

Replace the Abstract with:

A semiconductor device fabricating method includes ~~an amorphous silicon laminating process for~~ forming an amorphous silicon film ~~(2)~~ on a substrate ~~(1)~~, ~~an irradiation process for~~ irradiating the amorphous silicon film ~~(2)~~ with laser light ~~(16)~~ to transform at least a part of the amorphous silicon film ~~(2)~~ into a polycrystalline silicon film, and ~~an oxidation process for~~ oxidizing the surface of the polycrystalline silicon film in an atmosphere including oxygen, after the irradiation ~~process~~. ~~Herein, the~~ The laser light ~~(16)~~ is a linear beam having an energy-density gradient of at least $3 \text{ (mJ/cm}^2\text{)/}\mu\text{m}$ ~~or more in the a~~ widthwise direction, and the linear beam is generated by transforming ~~pulse~~ pulsed laser light with a wavelength in a range between 350 nm ~~or more~~ and 800 nm ~~or less~~. The oxidation ~~process~~ is performed in ~~an atmosphere of~~ a saturated water vapor ~~under~~ ambient at a pressure of at least 10 atmospheric pressures or more atmospheres and at a temperature in a range between 500°C ~~or more~~ and 650°C ~~or less~~. With this method, a semiconductor device with excellent crystallinity can be easily fabricated.